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## (54) HEAT DISSIPATING SUBSTRATE FOR SEMICONDUCTOR DEVICE AND ITS **MANUFACTURE**

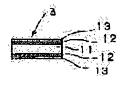
(57) Abstract:

(a)

PROBLEM TO BE SOLVED: To provide a heat dissipating substrate for semiconductor device which can be manufactured inexpensively by using a safe material and in which no defect is produced during the course of reliability tests.

SOLUTION: A heat dissipating substrate 3 for semiconductor device which is mounted on a package 1 for semiconductor device between a semiconductor element mounting section 2 and a semiconductor element 4 is formed by laminating upper and lower regenerated Au films 12, and upper and lower plated Au layers 13 upon both surfaces of an aluminum nitride substrate 11. The upper and lower plate Au layers 13 are formed in insulated states.

(b).



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